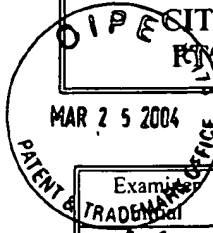
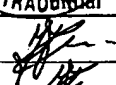

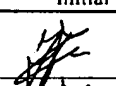
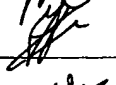
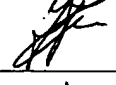

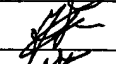



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| | Applicant(s): Katsuto TANAHASHI, et al. | |
| | Filing Date: December 24, 2003 | Group Art Unit: Unknown |


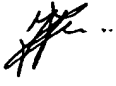
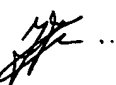
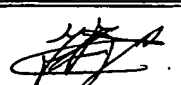
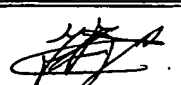
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